

Supplementary Information for

**Interdiffused Thermoplastic Urethane–PEDOT:PSS Bilayers with Superior Adhesion Properties for High–Performance and Intrinsically–Stretchable Organic Solar Cells**

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## **Experimental Section**

### **Materials**

PEDOT:PSS (Clevios PH1000 and Clevios P VP AI 4083) solutions were purchased from Heraeus. Perchloric acid (HClO<sub>4</sub>), chlorobenzene (CB), chloroform (CF), methanol, octadecyltrichlorosilane (ODTS), toluene, 3-glycidoxypropyltrimethoxysilane (GOPS), dimethylformamide (DMF), 1-chloronaphthalene (CN), 1,8-diiodooctane (DIO) and dimethyl Sulfoxide (DMSO) were purchased from Sigma-Aldrich. PM6, PCE12, Y6 and Y6-BO were purchased from Derthon. N2200 polymer (Mn: 150 k, PDI: 3.0) and PNDIT-F3N-Br were synthesized. TPU film was received from AFEL. Gallium (Ga, 99.99 % purity) and Indium (In, 99.99 % purity) were obtained from Taewon Scientific.

### **Preparation of acid-treated electrodes for transfer**

ODTS hydrophobic treatment was applied to the glass substrate to facilitate the transfer process. After immersing the plasma-treated glass substrate in a mixture of 50 ml of toluene and 60  $\mu$ l of ODTS at room temperature for 30 min, it was washed with acetone and dried in an oven at 80 °C. The PEDOT:PSS (doped with 0.5 vol.% of FS-30, 5 vol.% of DMSO and 0.15 vol.% of GOPS) solution was filtered through a 0.45  $\mu$ m polytetrafluorethylene (PTFE) filter, and then deposited on the ODTS treated glass substrate by spin-coating (1000 rpm) and dried at 100 °C in air (thickness: ~150 nm). 4 M HClO<sub>4</sub> solution was dropwise to the surface of the PEDOT:PSS film, and immediately washed with a spin-dry process, and dried on a hot plate at 100 °C for 15 min to remove residual acid (thickness: ~113 nm). For the molecular interdiffusion (MID)-assisted poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate)-thermoplastic urethane (PEDOT:PSS-TPU) layers, the TPU solution (dissolved in DMF at 450 mg mL<sup>-1</sup>) was spin-coated (4000 rpm) on acid-treated PEDOT:PSS and dried at 100 °C. In the

stamp transfer (ST) method, the pick-and-placed PEDOT:PSS bottom electrode layer was laid to the TPU film while slowly attaching/detaching the TPU film on an 80 °C hot plate.

### **Device Fabrication**

IS-OSCs were fabricated with TPU/acid-treated PEDOT:PSS/AI 4083/active layer/PNDIT-F3N-Br/eutectic gallium indium (EGaIn) structure. The transferred TPU/acid-treated PEDOT:PSS electrode was attached to a glass substrate for use as a bottom electrode. The hole transport layer (HTL, Clevios P VP AI 4083, doped with 0.5 vol.% of FS-30) was spin-coated at 3000 rpm (thickness: ~30 nm) on the plasma-treated bottom electrode and then annealed at 100 °C for 15 min. The active material was coated in a glove box. A blend of PM6:Y6-BO:N2200 with a weight ratio (1:1:0.15) was stirred for at least 3 h in CB at a total concentration of 24 mg mL<sup>-1</sup> and then spin-coated at 2500 rpm, 30 s (thickness: ~100 nm) on top of the TPU/acid-treated PEDOT:PSS/AI4083. A blend of PM6:Y6 (1:1.2, w/w) in CF (containing 0.5 vol% of 1-chloronaphthalene (CN)) with a total concentration of 13.5 mg mL<sup>-1</sup> solution was spuncast at 2500 rpm for 30 s (thickness: ~100 nm). A blend of PM6-OEG5:BTP-eC9 (1:1.2, w/w) in toluene (containing 0.5 vol% of DIO) with a total concentration of 18 mg mL<sup>-1</sup> solution was spuncast at 1500 rpm for 30 s (thickness: ~110 nm). A blend of PBDB-T:PYBDT-Cl (1:1, w/w) in CB with a total concentration of 20 mg mL<sup>-1</sup> solution was spun at 2000 rpm for 30 s (thickness: ~100 nm). All devices coated with the active layer were vacuum (< 10<sup>-5</sup> torr) dried for 1 h. Then, an electron transport layer (ETL, PNDIT-F3N-Br) solution (total concentration of 1 mg mL<sup>-1</sup> in methanol, stirred at room temperature for 3 h) was spin-coated at 3000 rpm for 30 s (thickness: ~5 nm) on the active layer. A top electrode, EGaIn, 75.5 wt% of Ga and 24.5 wt% of In were mixed at 80 °C. To pattern the electrodes, a liquid metal alloy was sprayed (thickness: ~100 μm) onto the ETL layer using a

shadow mask.

## **Characterizations**

The transmission spectrum of the PEDOT:PSS electrode was measured with a UV-vis spectrophotometer (UV-1800, Shimadzu). Sheet resistances of the PEDOT:PSS films were measured by using a four point probe. The ultraviolet photoelectron spectroscopy (UPS) profiles were obtained by Sigma Probe from Thermo VG Scientific Thermo VG Scientific incorporation. The 90 ° peel tests were performed using an adhesion tester (DTS company, 50 lbf load cell) operated at a peeling rate of 0.1 mm s<sup>-1</sup> with an adhesive tape (12 mm width). The time-of-flight secondary ion mass spectrometry (TOF-SIMS) depth profiling analysis (sputtered with 5 keV Ar<sup>+</sup> and 500 × 500 μm<sup>2</sup>) was performed to investigate the interfacial properties between the PEDOT:PSS electrode and the TPU. Relative resistance (R/R<sub>0</sub>) and tensile cycle test of PEDOT:PSS film were measured using a stretching tester (JIRBT-620, Junil Tech., South Korea). Atomic force microscopy (AFM, Parks Systems NX20) was used to analyze the surface morphology of PEDOT:PSS film. To measure the thickness of PEDOT:PSS film, we used a surface profiler (Tencor α-Step IQ). The PCE was determined under ambient conditions with a solar simulator (K201 LAB55, McScience). The photovoltaic performance was measured under air mass 1.5 solar illumination at 100 mW cm<sup>-2</sup> (1 sun). The intensity of the solar simulator was calibrated using a standard silicon reference cell (K801S-K302, McScience). The current density-voltage (*J-V*) characteristics were recorded using a Keithley 2400 SMU semiconductor characterization system. A shadow mask (0.04 cm<sup>2</sup>) was used to define the photoactive area during the measurements. And, we measured the change in properties of IS-OSCs according to elongational deformation using a manually adjustable tensile strain test holder. External quantum efficiency (EQE) spectra were measured by K3100

15 IQX (McScience Inc.) and MC 2000 optical chopper (Thorlabs) under ambient conditions.

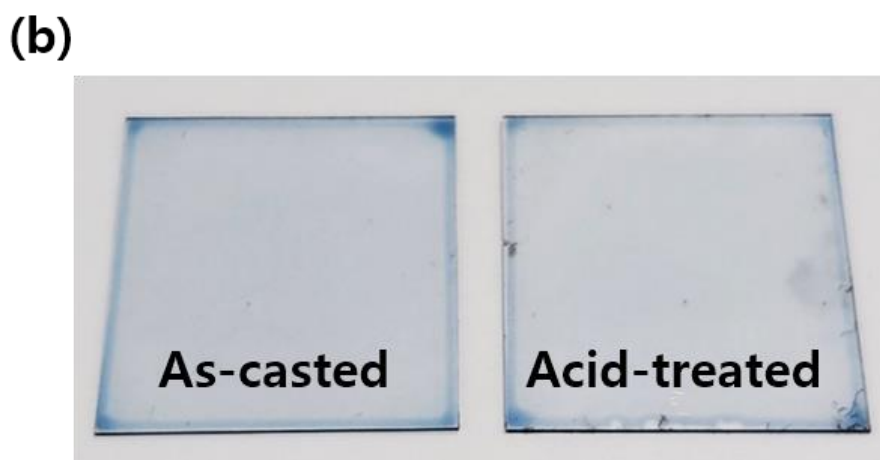
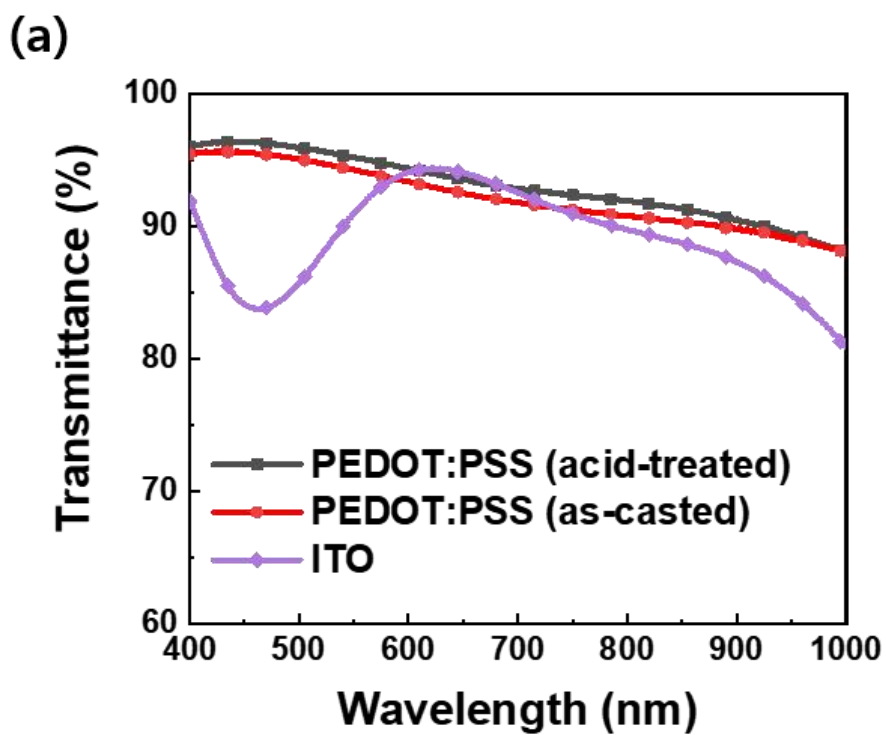
### Calculation of FoM value

The FoM is defined as the ratio of direct current conductivity ( $\sigma_{dc}$ ) to optical conductivity ( $\sigma_{op}$ ). It can be calculated as sheet resistance ( $\Omega \text{ sq}^{-1}$ ), transmittance (%), at  $\lambda = 550 \text{ nm}$  and impedance of free space ( $Z_0, 377 \Omega$ ).

$$FoM = \frac{\sigma_{dc}}{\sigma_{op}} = \frac{Z_0}{2R_{sheet} \left( T^{-\frac{1}{2}} - 1 \right)}$$

### Finite Element Method Simulation

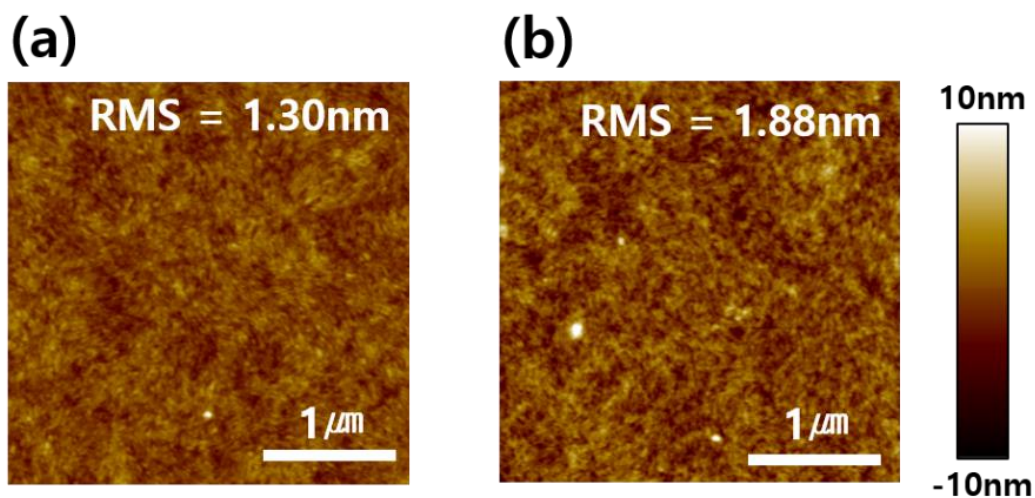
The relationship between the stretchability and the interfacial adhesion was investigated using a commercial finite element method tool (ABAQUS v 6.24). The TPU-PEDOT:PSS bilayer was modeled as a deformable 3D solid with 226,929 nodes and 210,160 elements of type CSD8R (8-node linear brick, reduced integration, hourglass control). The TPU was considered as a hyperelastic material based on the Arruda-Boyce model (E: 10 MPa,  $\nu$ : 0.45), while the PEDOT:PSS was considered to be elastic material (E: 500 MPa,  $\nu$ : 0.35). To simulate the stretching and cracking process, the boundary conditions of the model were defined as follows: The model was uniaxially tensile loaded with displacement control, and the interfacial adhesion was characterized with a fracture criterion of VCCT. And, planar crack driving force was calculated for a 10  $\mu\text{m}$  long initial crack with the J-integral method.



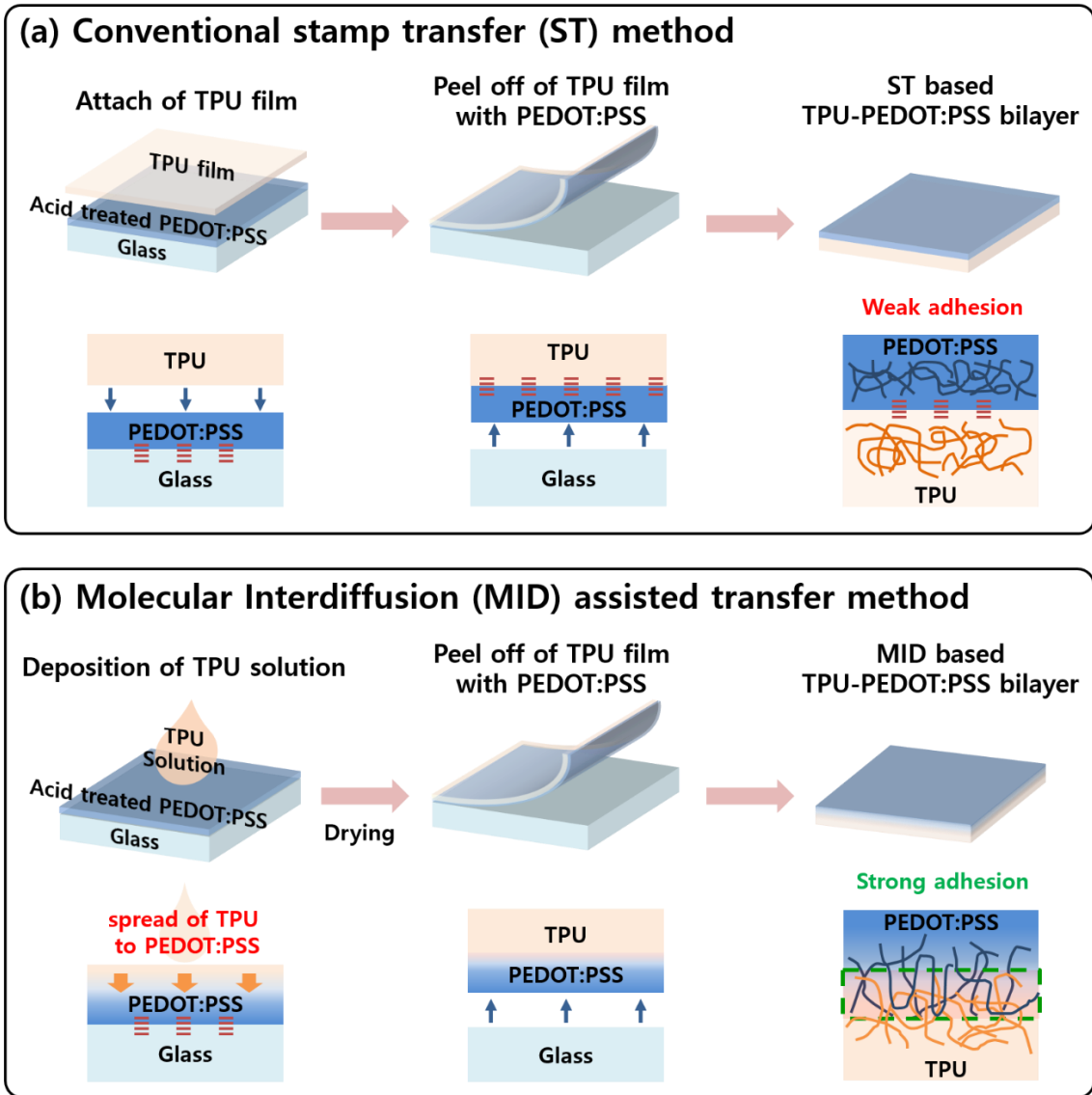
**Fig. S1.** (a) Optical transmittances of as-casted and acid-treated PEDOT:PSS STEs compare with ITO; (b) images of as-casted and acid-treated PEDOT:PSS on ODTS treated glass.

**Table S1.** Sheet resistance, conductivity and work function of PEDOT:PSS depending on acid treatment and transfer method.

	Substrate	sheet resistance ( $\Omega \text{ sq}^{-1}$ )	conductivity ( $\text{S cm}^{-1}$ )	work function (eV)
<b>PEDOT:PSS as-casted</b>	glass	110	605	5.0
	glass	92	961	5.0
<b>PEDOT:PSS acid-treated</b>	TPU (MID)	88	959	5.0
	TPU (ST)	90	958	5.0

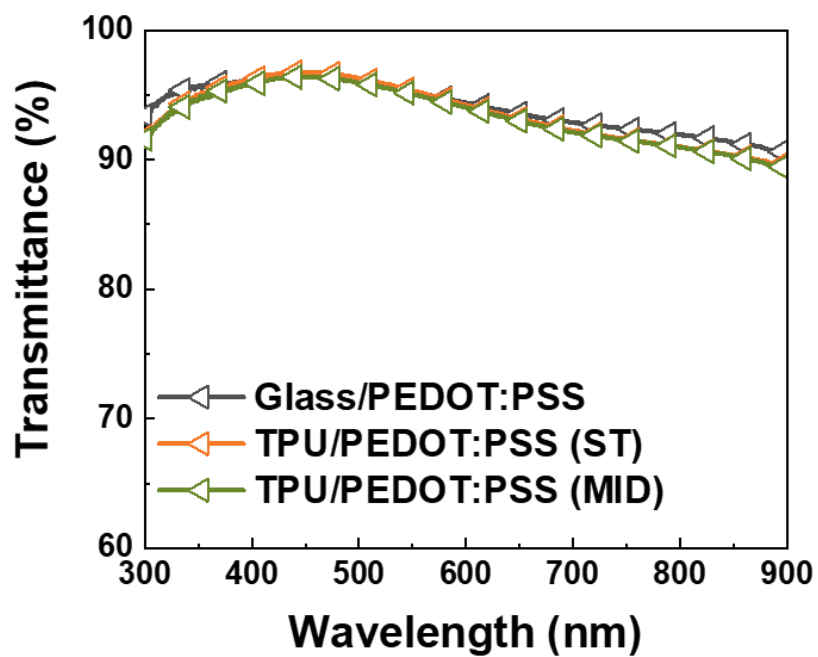


**Fig. S2.** AFM images of (a) as-casted PEDOT:PSS and (b) acid-treated PEDOT:PSS.

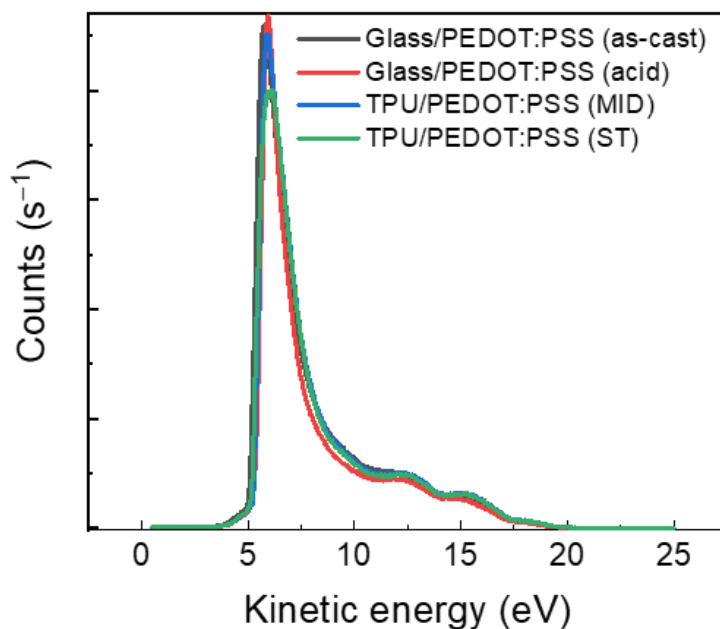


**Fig. S3.** Schematics depicting fabrication procedures of (a) ST- and (b) MID-based TPU-PEDOT:PSS bilayers.

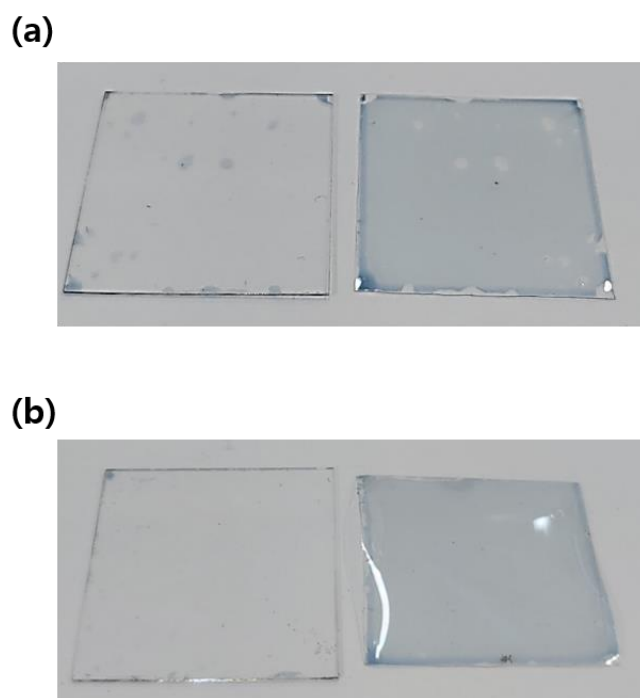




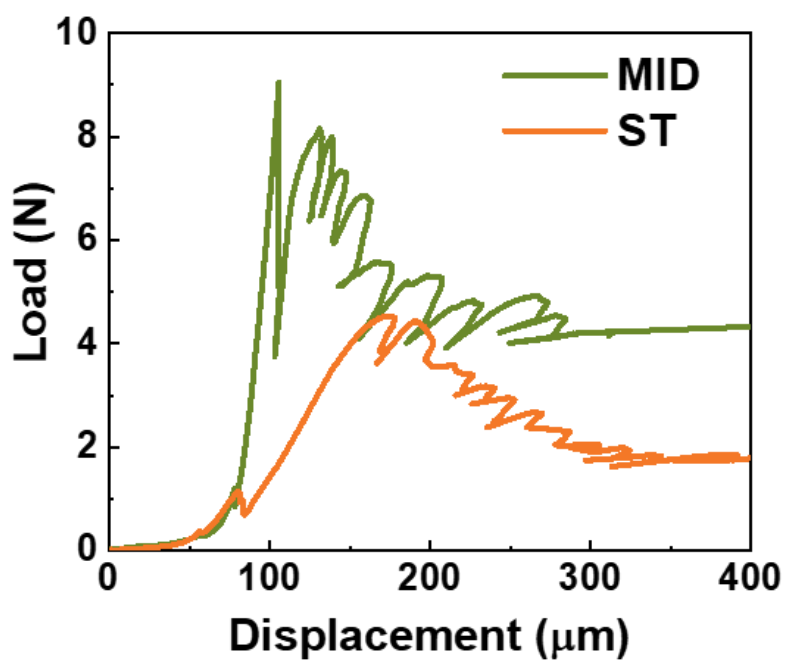
**Fig. S4.** Optical transmittance of PEDOT:PSS STEs on bare glass and on TPU films (ST and MID-assisted).



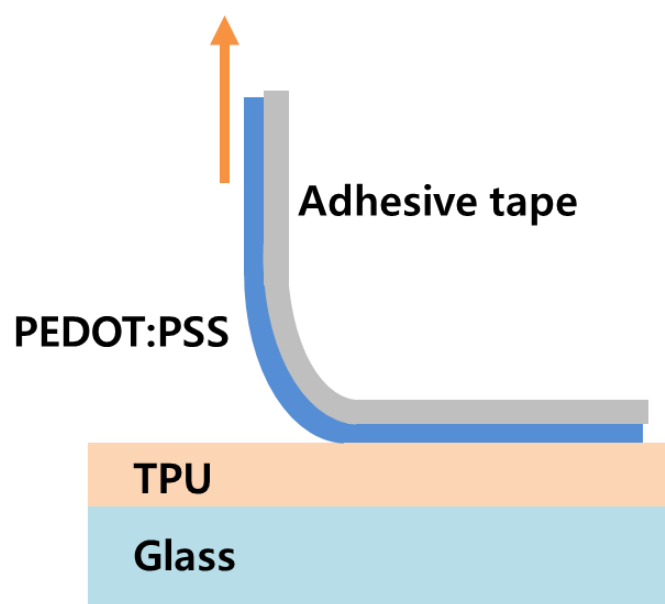
**Fig. S5.** UPS (Ultraviolet photoelectron spectroscopy) profiles of PEDOT:PSS depending on acid treatment and transfer method.



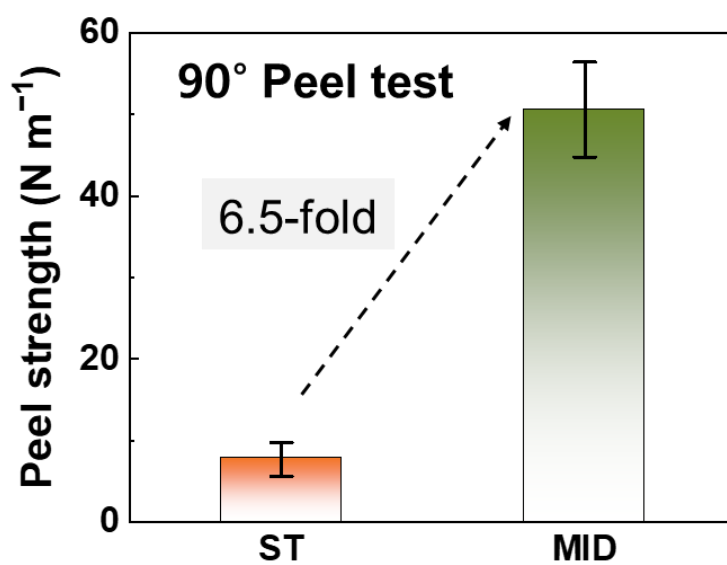
**Fig. S6.** The photographs of (a) ST- and (b) MID-assisted TPU-PEDOT:PSS bilayers (right) from glass substrates (left).



**Fig. S7.** Displacement vs. load profiles of ST- and MID-based TPU-PEDOT:PSS bilayers measured by DCB test.

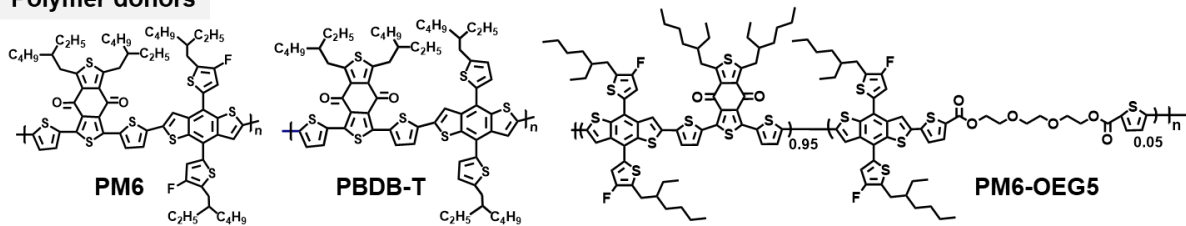


**Fig. S8.** Schematic diagram for the 90° peel test.

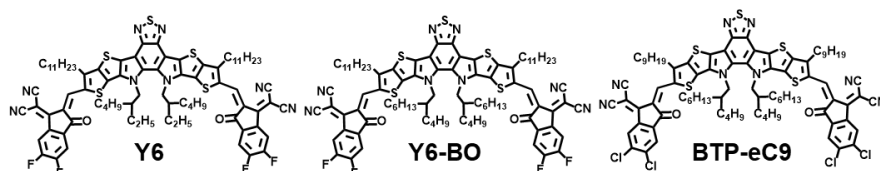


**Fig. S9.** Peel strength of ST- and MID-based bilayers measured from 90° peel test.

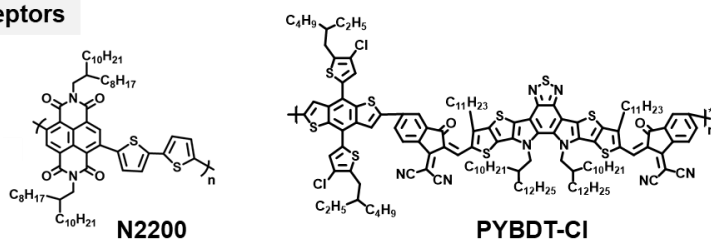
### Polymer donors



### Small-molecule acceptors



### Polymer acceptors



**Fig. S10.** Chemical structures of the active materials used in this study.

**Table S3.** Photovoltaic parameters of the PM6:Y6-BO:N2200-based IS-OSCs with MID-based TPU-PEDOT:PSS as a function of strain.

<b>Strain (%)</b>	<b><math>V_{oc}</math> (V)</b>	<b><math>J_{sc}</math> (mA cm<sup>-2</sup>)</b>	<b>FF (%)</b>	<b>PCE (%)</b>
0	0.85	23.2	65.9	13.1
10	0.86	23.1	67.4	13.4
20	0.86	23.3	66.9	13.5
30	0.86	23.8	61.7	13.0
40	0.85	22.3	55.3	9.4
50	0.85	19.7	44.3	7.5

**Table S4.** Photovoltaic parameters of the PM6:Y6-BO:N2200-based IS-OSCs with ST-based TPU-PEDOT:PSS as a function of strain.

<b>Strain (%)</b>	<b><math>V_{oc}</math> (V)</b>	<b><math>J_{sc}</math> (mA cm<sup>-2</sup>)</b>	<b>FF (%)</b>	<b>PCE (%)</b>
0	0.85	23.0	67.8	13.3
10	0.87	22.9	64.6	12.7
20	0.88	22.5	59.3	11.7
30	0.87	21.8	45.3	8.6
40	0.87	19.9	36.7	6.4
50	0.86	14.7	31.6	4.0

**Table S5.** Photovoltaic parameters of the PM6:Y6-based IS-OSCs with MID-based TPU-PEDOT:PSS as a function of strain.

<b>Strain (%)</b>	<b><math>V_{oc}</math> (V)</b>	<b><math>J_{sc}</math> (mA cm<sup>-2</sup>)</b>	<b>FF (%)</b>	<b>PCE (%)</b>
0	0.81	20.44	63.54	10.56
10	0.82	20.50	63.00	10.65
20	0.82	20.33	63.53	10.61
30	0.83	19.62	48.48	7.86
40	0.80	7.92	35.18	2.22
50	0.78	4.05	35.52	1.12

**Table S6.** Photovoltaic parameters of the PM6:Y6-based IS-OSCs with ST-based TPU-PEDOT:PSS as a function of strain.

<b>Strain (%)</b>	<b><math>V_{oc}</math> (V)</b>	<b><math>J_{sc}</math> (mA cm<sup>-2</sup>)</b>	<b>FF (%)</b>	<b>PCE (%)</b>
0	0.85	20.38	60.40	10.52
10	0.85	20.35	59.16	10.24
20	0.85	20.09	51.25	8.75
30	0.53	13.21	31.87	2.23
40	0.51	12.95	29.53	1.95
50	0.41	10.68	24.22	1.06

**Table S7.** Photovoltaic parameters of the PM6-OEG5:BTP-eC9-based IS-OSCs with MID-based TPU-PEDOT:PSS as a function of strain.

<b>Strain (%)</b>	<b><math>V_{oc}</math> (V)</b>	<b><math>J_{sc}</math> (mA cm<sup>-2</sup>)</b>	<b>FF (%)</b>	<b>PCE (%)</b>
0	0.86	23.43	63.08	12.69
10	0.86	23.69	63.96	13.03
20	0.86	23.99	61.70	12.74
30	0.85	20.57	57.45	10.02
40	0.84	22.59	49.21	9.31
50	0.82	19.52	43.41	6.98

**Table S8.** Photovoltaic parameters of the PM6-OEG5:BTP-eC9-based IS-OSCs with ST-based TPU-PEDOT:PSS as a function of strain.

<b>Strain (%)</b>	<b><math>V_{oc}</math> (V)</b>	<b><math>J_{sc}</math> (mA cm<sup>-2</sup>)</b>	<b>FF (%)</b>	<b>PCE (%)</b>
0	0.85	23.48	62.10	12.38
10	0.84	23.25	62.10	12.11
20	0.85	22.52	58.37	11.11
30	0.82	14.56	37.81	4.52
40	0.83	10.57	25.46	2.24
50	0.82	9.16	19.87	1.49

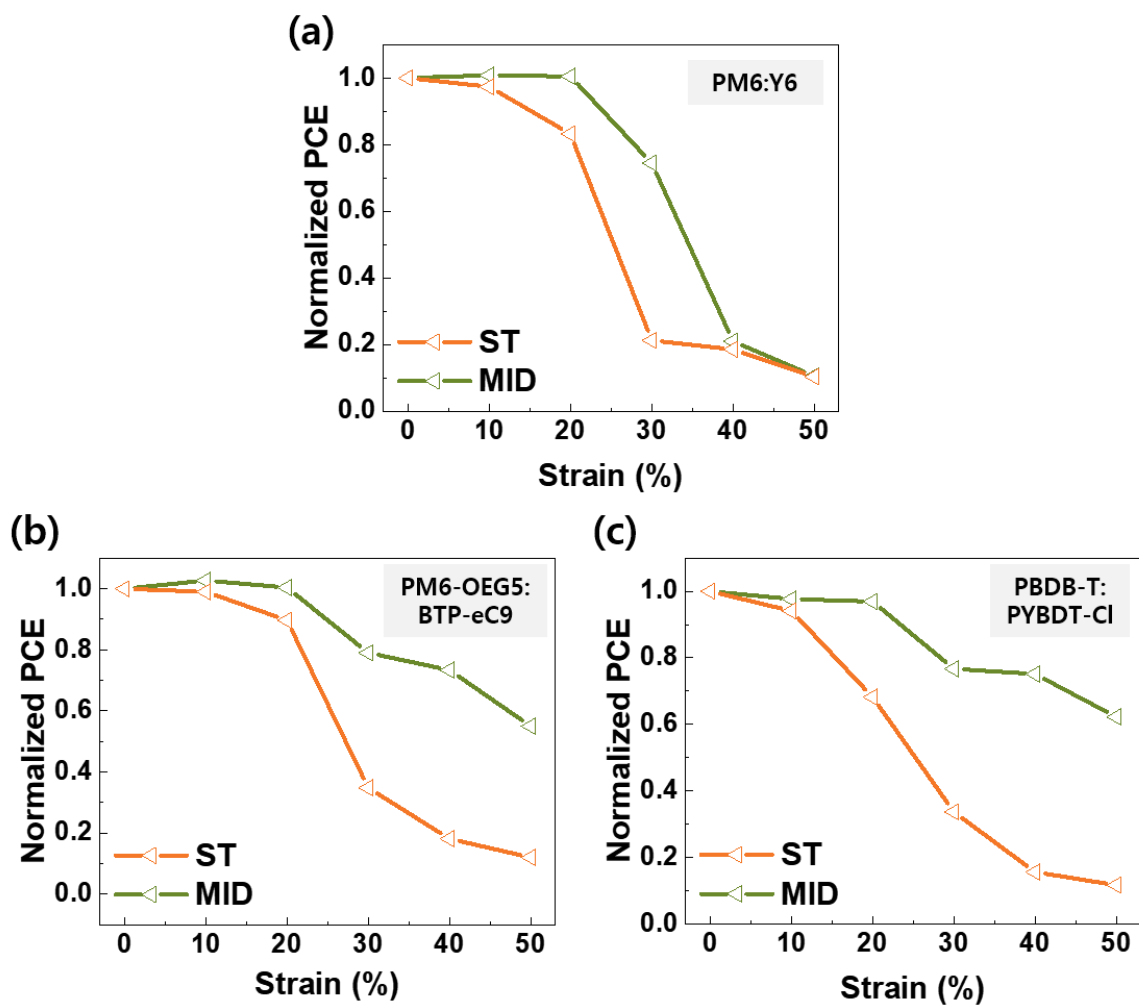
**Table S9.** Photovoltaic parameters of the PBDB-T:PYBDT-Cl-based IS-OSCs with MID-based TPU-PEDOT:PSS as a function of strain.

<b>Strain (%)</b>	<b><math>V_{oc}</math> (V)</b>	<b><math>J_{sc}</math> (mA cm<sup>-2</sup>)</b>	<b>FF (%)</b>	<b>PCE (%)</b>
0	0.89	17.77	67.74	10.77
10	0.89	18.00	65.54	10.52
20	0.90	16.51	70.30	10.44
30	0.88	15.41	61.14	8.26
40	0.88	15.91	58.08	8.09
50	0.84	15.63	50.84	6.70

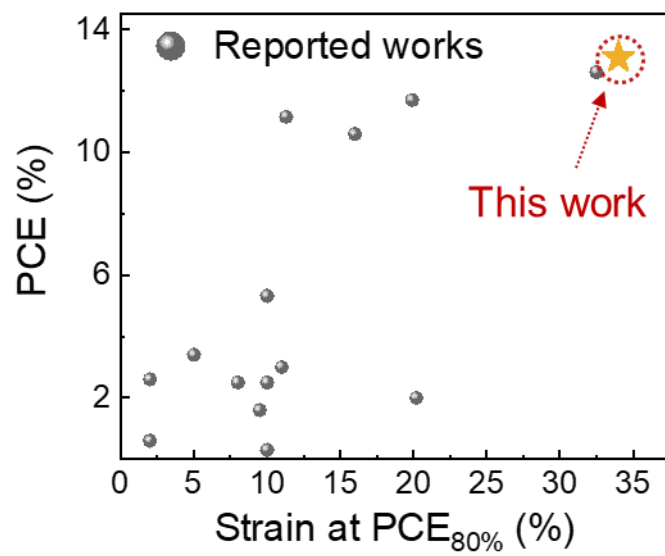
**Table S10.** Photovoltaic parameters of the PBDB-T:PYBDT-Cl-based IS-OSCs with ST-based TPU-PEDOT:PSS as a function of strain.

<b>Strain (%)</b>	<b><math>V_{oc}</math> (V)</b>	<b><math>J_{sc}</math> (mA cm<sup>-2</sup>)</b>	<b>FF (%)</b>	<b>PCE (%)</b>
0	0.90	18.39	69.93	11.53
10	0.90	17.04	70.95	10.85
20	0.88	15.26	58.28	7.86
30	0.69	14.47	38.94	3.88
40	0.45	11.78	34.05	1.79
50	0.42	9.77	32.74	1.34





**Fig. S11.** PCE of (a) PM6:Y6, (b) PM6-OEG5:BTP-eC9 and (c) PBDB-T:PYBDT-Cl based IS-OSCs under strains.



**Fig. S12.** PCE versus strain plots for IS-OSCs from the reported studies and this study.

**Table S11.** Device structures, mechanical and photovoltaic performances of reported IS-OSCs. The PCE<sub>80%</sub> values were estimated by interpolation of the data reported in the papers.

Year	Device structure	Active Layer	PCE [%]	Strain at PCE <sub>80%</sub> [%]	Ref.
2012	UV/O <sub>3</sub> -treated PDMS/PEDOT:PSS/Active Layer/EGaIn	P3HT:PCBM	~1	-	1
		P3DDT:PCBM	0.59	-	2
2013	PDMS/PEDOT:PSS/Active Layer/EGaIn	P3HT:PCBM	0.59	-	2
2016	PU/PEDOT:PSS/PEI/Active Layer/PEDOT:PSS/PU	P3HpT:PCBM	1.25	-	3
2017	PUA-AgNW/SWNT/PEDOT:PSS/Active Layer/PEIE/SWNT/AgNW-PUA	PTB7-Th:PC <sub>71</sub> BM	2.90	-	4
		PTB7-Th:PCBM	5.32	8.1	5
2017	3M tape/PEI/Ag/PH1000/Active Layer/EGaIn	PTB7-Th:N2200	2.02	20.2	5
		PTB7-Th:N2200	2.02	20.2	
2018	3M tape/PEDOT:PSS/Active Layer/PFN-NBR/EGaIn	PTB7-Th:ITIC	1.66	10.4	6
		PTB7-Th:P(NDI2HD-T)	3.00	15.7	
2019	Ag mesh/PEDOT:PSS/Active Layer/PEIE/Ag/Parylene	PTzNTz: PC <sub>71</sub> BM	9.70	7.7	7
2021	PDMS/PH1000/Active Layer/EGaIn	PBDB-T:PCE10:N2200 (1.2:0.8:1)	6.33	11.2	8
		PM6:Y7	11.2	12.4	9
2021	TPU/PH1000/AI4083/Active Layer/PNDIT-F3N-Br/EGaIn	PM6:PCBM	5.7	5.1	
		PCE12:N2200	5.0	42.3	
2021	TPU/AgNW/PEDOT:PSS/Active Layer/EGaIn	PTB7-Th:IEICO-4F	10.1	12.0	10
2022	TPU/PH1000/AI4083/Active Layer/PNDIT-F3N-Br/EGaIn	PM6:Y7:N2200 (1:0.8:0.2)	11.71	19.9	11
2022	TPU/PH1000/AI4083/Active Layer/PNDIT-F3N-Br/EGaIn	PhAm5:Y7	12.7	31.6	12
2022	MID-based TPU-PEDOT:PSS/AI4083/Active Layer/PNDIT-F3N-Br/EGaIn	PM6:Y6-BO:N2200	<b>13.1</b>	<b>34.0</b>	<b>This Work</b>

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